

Low Saturation PNP Epitaxial Planar Transistor

BTB589N3

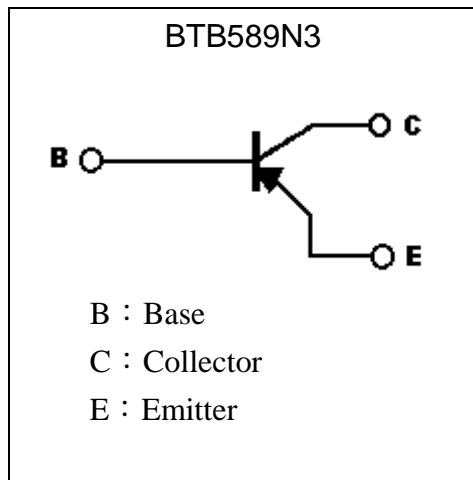
Description

The BTB589N3 is designed with high current gain and low saturation voltage with collector current up to 1A continuous.

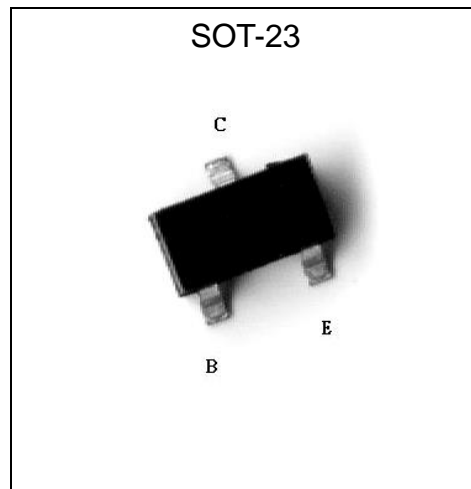
Features

- Low $V_{CE(SAT)}$, $V_{CE(SAT)} \leq -0.3V$ ($I_C / I_B = -1A / -100mA$)
- Large collector current, $I_C = -1A$
- Pb-free lead plating and halogen-free package

Symbol

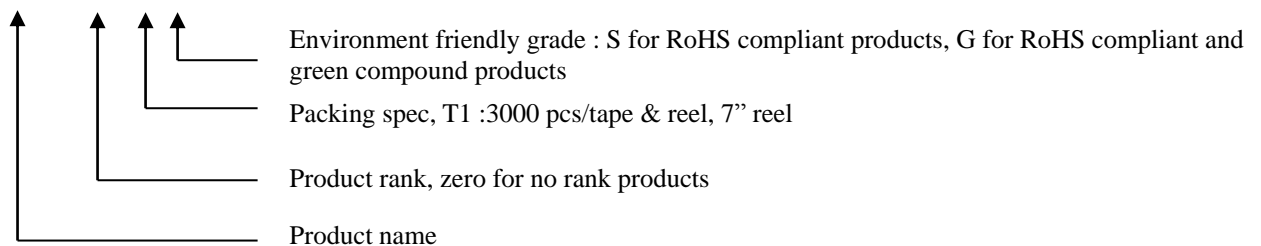


Outline



Ordering Information

Device	Package	Shipping
BTB589N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-1	A
Collector Current (Pulse)	I _{CP}	-2	
Power Dissipation	P _D	310 (Note 1)	mW
		500 (Note 2)	
Operating Junction Temperature Range	T _j	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-ambient, max	R _{θJA}	403 (Note 1)	°C/W
		250 (Note 2)	

Note: 1.Device mounted on FR-4 PCB with minimum pad
 2.Device mounted on FR-4 PCB with area of 4.5"×5", mounting pad 0.02 in² of 2 oz copper

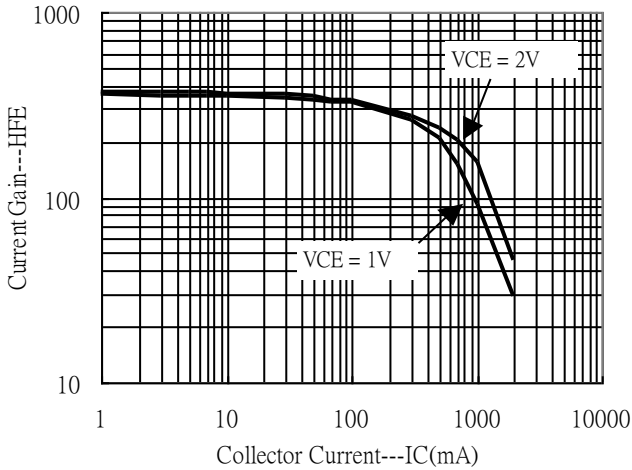
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
B _V CB0	-40	-	-	V	I _C =-50μA
B _V CEO	-32	-	-	V	I _C =-1mA
B _V EBO	-5	-	-	V	I _E =-50μA
I _{CB0}	-	-	-100	nA	V _{CB} =-30V
I _{EBO}	-	-	-100	nA	V _{EB} =-4V
*V _{CE(sat)} 1	-	-	-0.25	V	I _C =-500mA, I _B =-50mA
*V _{CE(sat)} 2	-	-	-0.30	V	I _C =-1A, I _B =-100mA
*V _{CE(sat)} 3	-	-	-0.65	V	I _C =-2A, I _B =-200mA
*V _{BE(sat)}	-	-	-1.2	V	I _C =-1A, I _B =-100mA
*V _{BE(on)}	-	-	-1.1	V	V _{CE} =-2V, I _C =-1A
*h _{FE} 1	180	-	420	-	V _{CE} =-3V, I _C =-100mA
*h _{FE} 2	100	-	-	-	V _{CE} =-2V, I _C =-500mA
*h _{FE} 3	80	-	-	-	V _{CE} =-2V, I _C =-1A
*h _{FE} 4	30	-	-	-	V _{CE} =-2V, I _C =-2A
f _T	100	200	-	MHz	V _{CE} =-5V, I _C =-50mA, f=100MHz
C _{ob}	-	12	25	pF	V _{CB} =-10V, f=1MHz

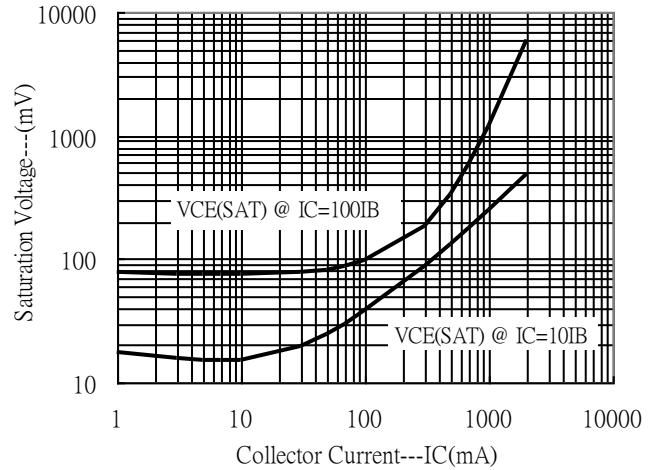
*Pulse Test: Pulse Width ≤380μs, Duty Cycle ≤2%

Typical Characteristics

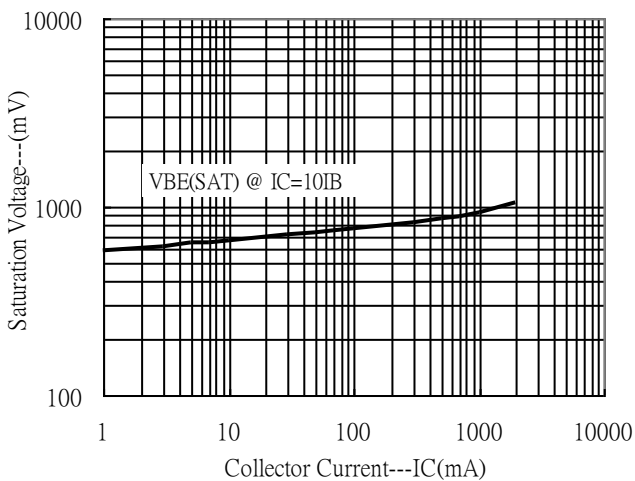
Current Gain vs Collector Current



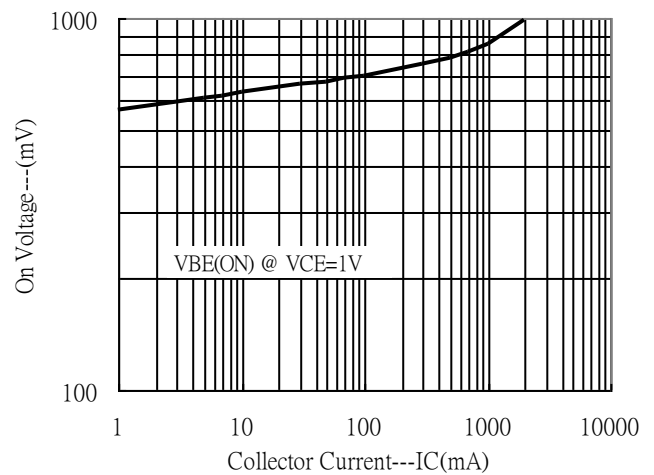
Saturation Voltage vs Collector Current



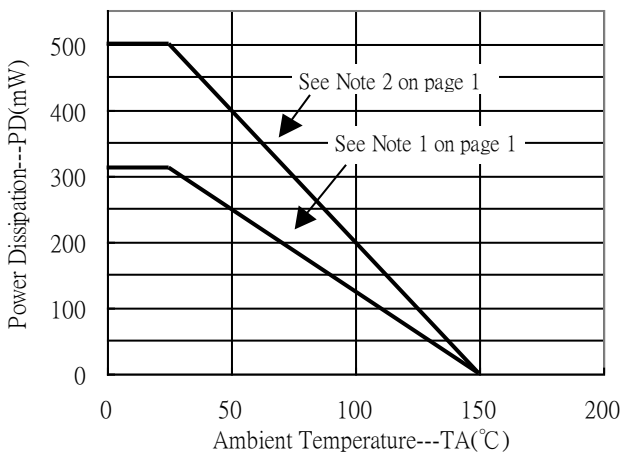
Saturation Voltage vs Collector Current



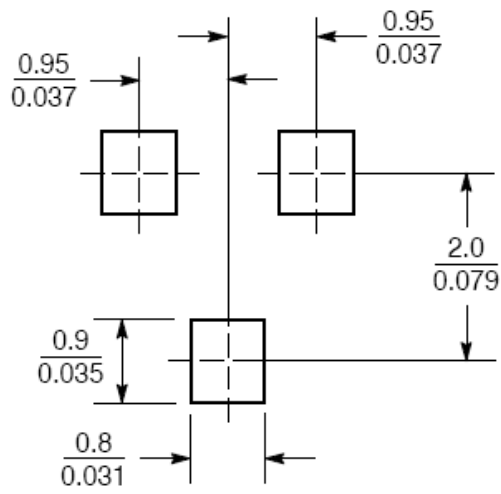
On Voltage vs Collector Current



Power Derating Curves

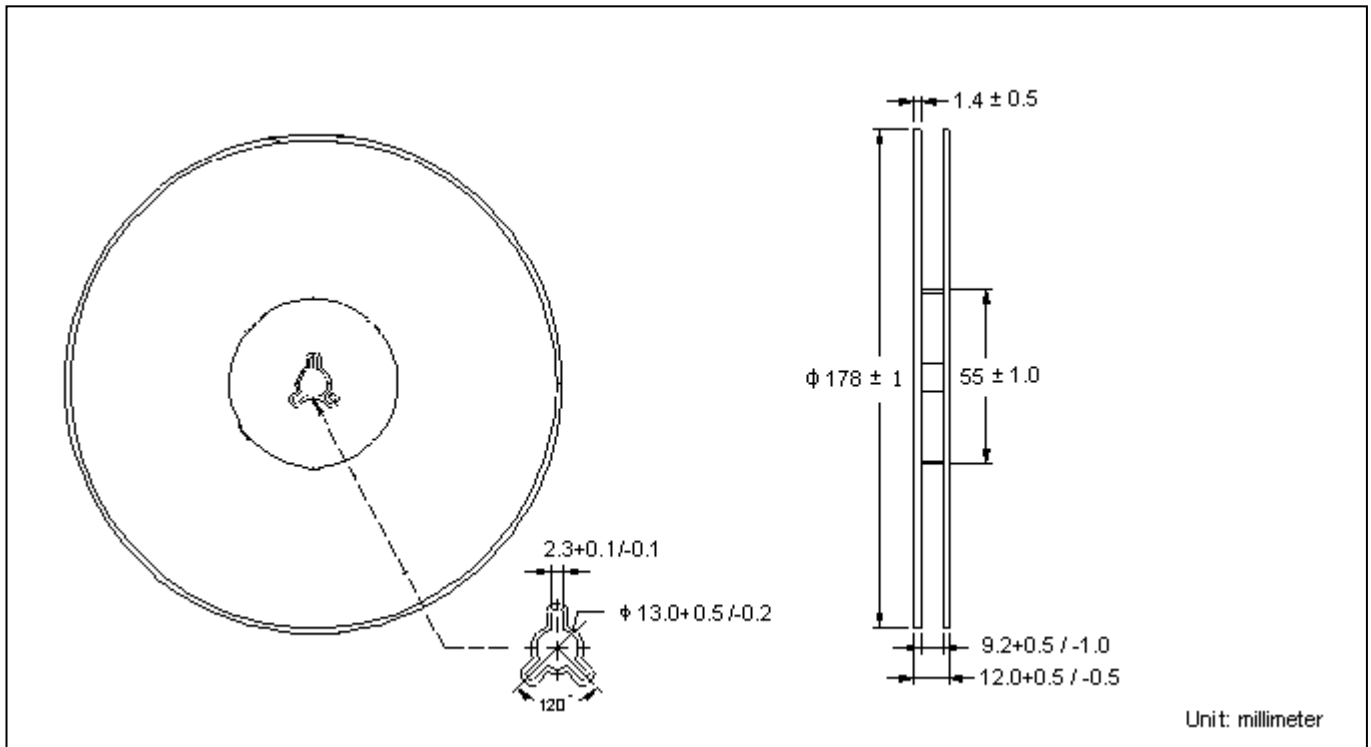


Recommended Soldering Footprint

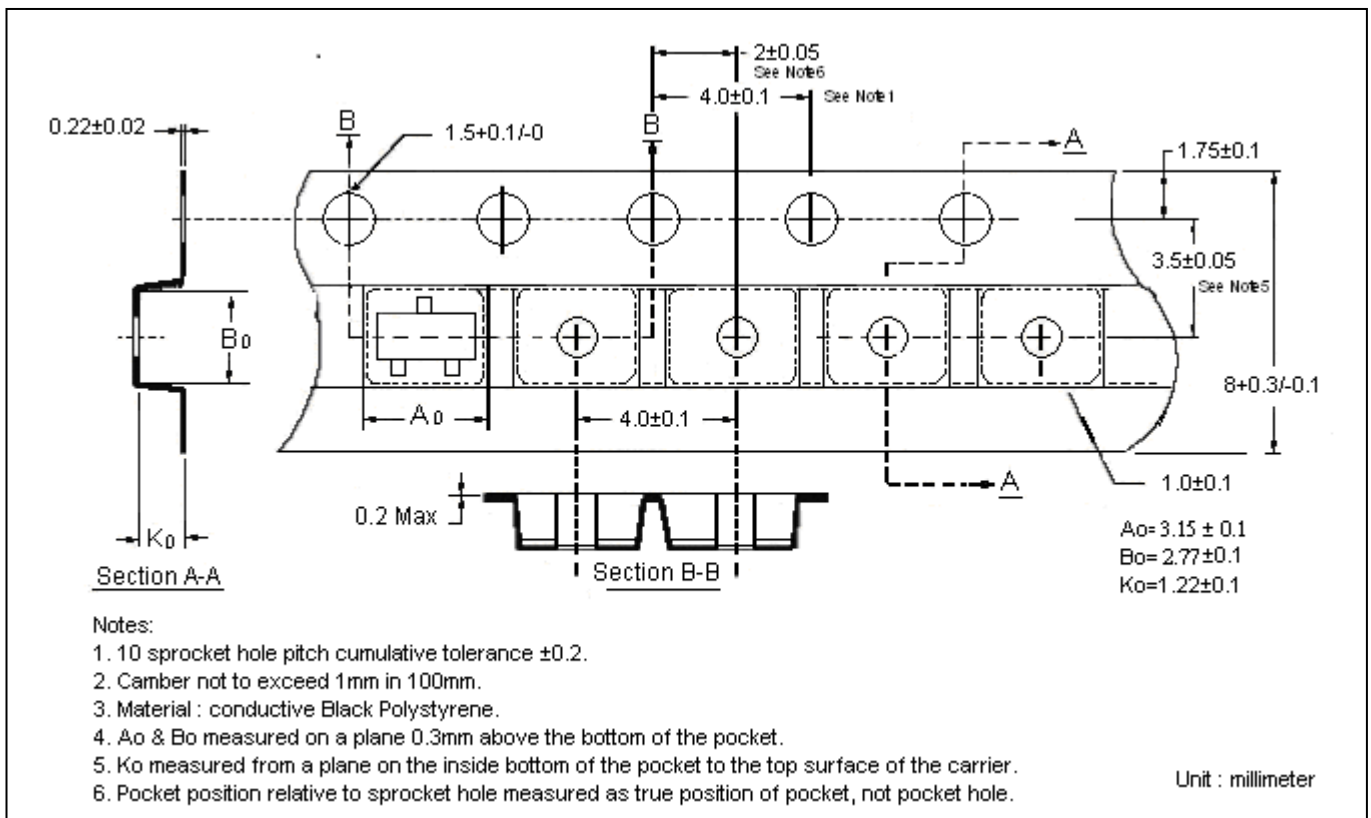


Unit : $\frac{\text{mm}}{\text{inches}}$

Reel Dimension



Carrier Tape Dimension



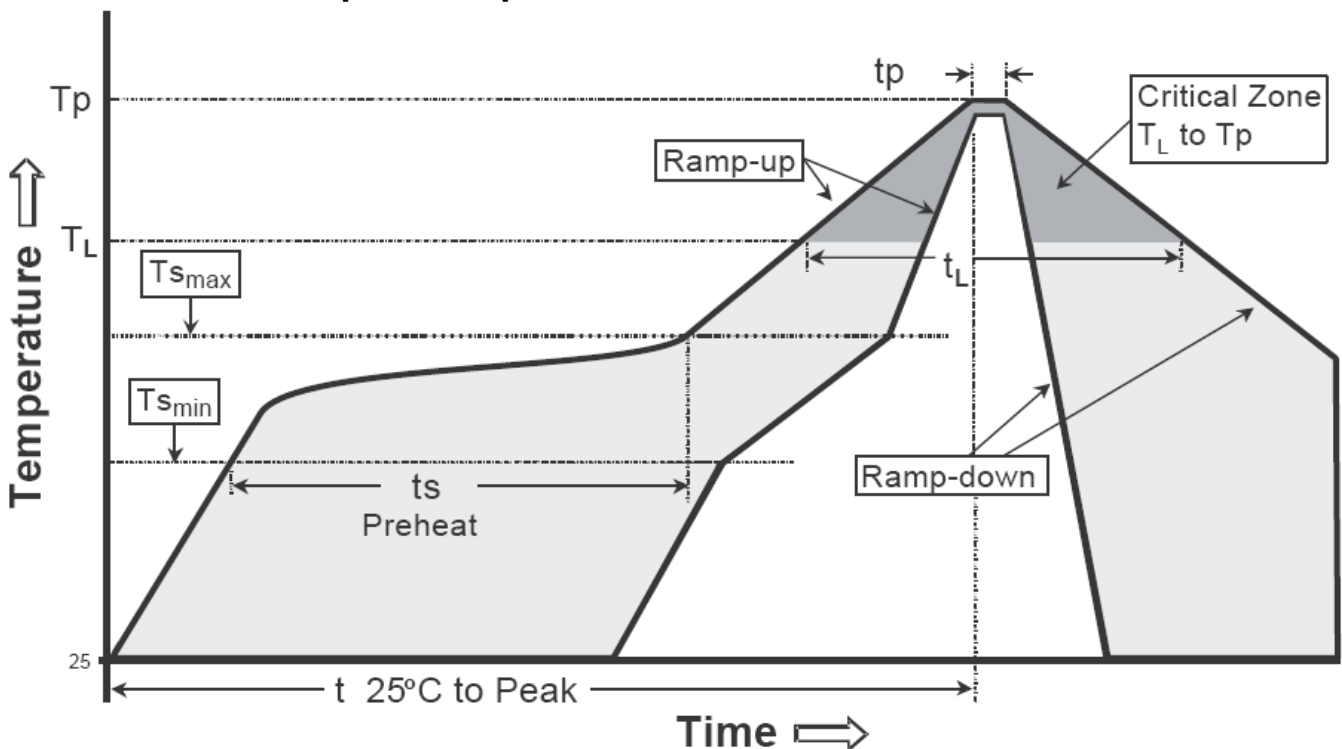
Notes:

1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. A_0 & B_0 measured on a plane 0.3mm above the bottom of the pocket.
5. K_0 measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

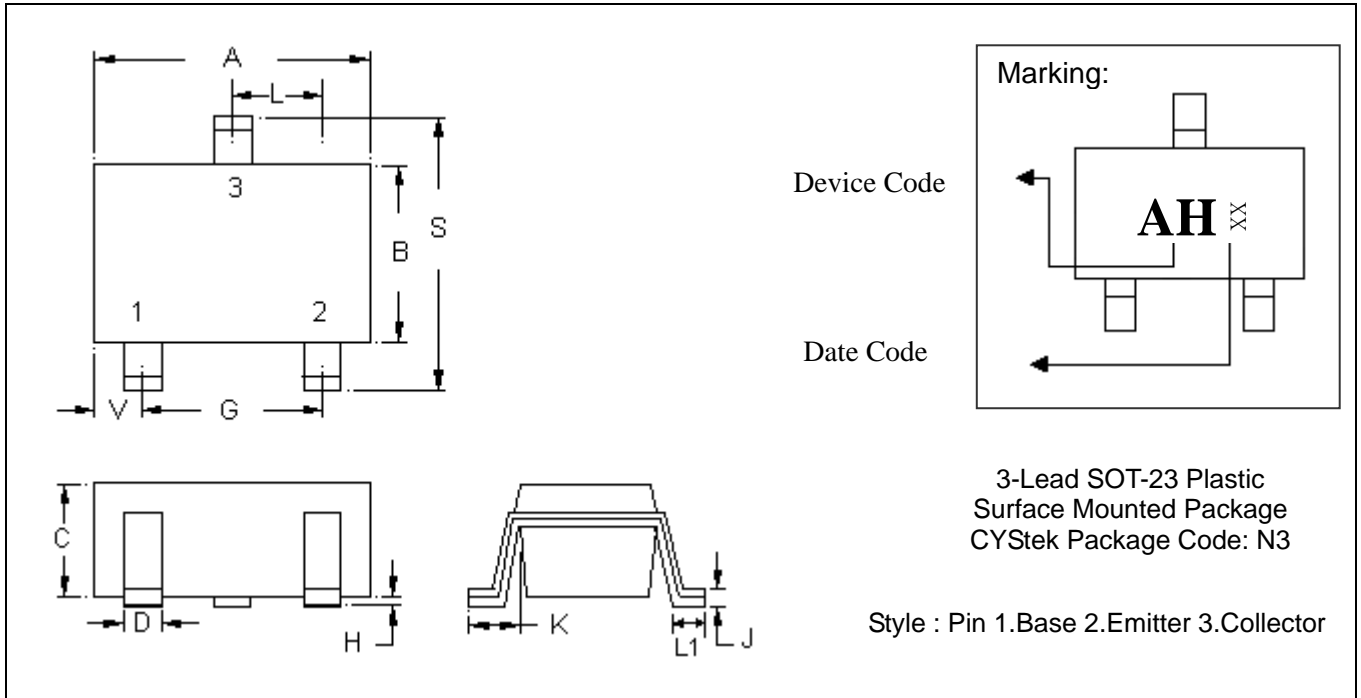
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0551	1.20	1.40	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1004	2.10	2.55
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50

- Notes :
- 1.Controlling dimension : millimeters.
 - 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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